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A two-dimensional hybrid with molybdenum disulfide nanocrystals strongly coupled on nitrogen-enriched graphene *via* mild temperature pyrolysis for high performance lithium storage[†]

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A novel 2D hybrid with MoS₂ nanocrystals strongly coupled on nitrogen-enriched graphene (MoS₂/NG_{g-C₃N₄) is realized by mild temperature pyrolysis (550 °C) of a self-assembled precursor (MoS₃/g-C₃N₄-H⁺/GO). With rich active sites, the boosted electronic conductivity and the coupled structure, MoS₂/NG_{g-C₃N₄ achieves superior lithium storage performance.}}

Nowadays, portable electronics and commercial electric vehicles (EVs) are mostly powered by lithium ion batteries (LIBs).¹ However, the energy and power densities of LIBs with a conventional graphite anode still lag behind the increasing requirements. The emergence of graphene with excellent charge carrier mobility, large specific surface area and strong mechanical properties² has provided amazing opportunities for high performance LIBs, as it can serve as an intriguing two-dimensional (2D) platform to hybridize with various lithium storage components.^{3–6} In particular, nitrogen doping confers an important strategy to impart graphene with enhanced electronic conductivity, additional active sites for lithium storage, and improved affinity to other integrants.^{7–13} Diverse approaches have been developed to dope nitrogen into carbon networks including chemical vapor deposition (CVD),^{8,9,14} plasma treatment,^{15,16} arc-discharge,¹⁷ hydro-thermal process,^{12,13,18–21} and thermal conversion of nitrogen-rich precursors.^{7,10,11,22-28} Nevertheless, harsh conditions such as high temperature (700-1100 °C),^{8-11,14,17,22-28} high vacuum,^{7,15,16} or high pressure^{12,13,18-21} are generally required in these methods. Meanwhile, the nitrogen content in graphene is usually lower than 10 at%. Thereby, the scalable production of

hybrids based on nitrogen-enriched graphene remains a big challenge.

With favorable interlayer spacing for Li insertion/extraction, molybdenum disulfide (MoS₂), a layered transition metal dichalcogenide, is regarded as a promising candidate to compose graphene-based hybrids as anode materials in LIBs.²⁹ Along this line, various hybrids with MoS₂ and graphene nanosheets have been fabricated *via* methods including exfoliation and restacking,^{30–32} CVD,³³ and hydrothermal reaction.^{11,34–39} However, insufficient Li storage sites and the poor intrinsic electrical conductivity among MoS₂ layers are still difficult to conquer, hampering their electrochemical performances in LIBs. Thus, the integration of nanosized MoS₂ on N-doped graphene with strong synergies is envisioned to provide rich lithium storage sites and the coupled structure with the enhanced conductivity for high cycling/rate performance.

In this work, we demonstrate an efficient approach towards a novel 2D mesoporous nanohybrid with MoS₂ nanocrystals strongly coupled on nitrogen-enriched graphene (MoS₂/ $NG_{g-C_2N_4}$, which is derived from the mild temperature pyrolysis (550 °C) of the self-assembled tri-constituent composite with molybdenum trisulfide (MoS₃), protonated graphitic carbon nitride $(g-C_3N_4-H^+)$ and graphene oxide (GO). During the thermal treatment, $g-C_3N_4-H^+$ effectively assists the formation of highly crystallized MoS2 nanoplatelets with sizes smaller than 10 nm and (002) d-spacing of 0.66 nm vertically exposed on the graphene surface, resulting in a mesoporous structure with a high specific surface area and a large pore volume (109 m² g⁻¹, 0.883 cm³ g⁻¹) of the 2D hybrid. Simultaneously, molybdenum sulfide promotes the complete decomposition of g-C₃N₄-H⁺ at mild temperature and thereby imparts graphene with a high content of N dopants (ca. 13 at.%), rendering greatly enhanced coupling of MoS2 on the N-enriched graphene and boosting the conductivity of the hybrid. As a consequence, $MoS_2/NG_{g\text{-}C_3N_4}$ manifests the outstanding reversible capacity (1450 mA h g^{-1} at 0.1 A $g^{-1})$ for 200 cycles and exceptional rate capability (1200 mA h g^{-1} at 1A g^{-1} , 830 mA h g^{-1} at

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[†]Electronic supplementary information (ESI) available: Photo images, Zeta potential, additional SEM, TEM, HRTEM and AFM images, XRD, FTIR, TGA under N2, TGA under air, pore size distribution, additional XPS are presented. N doping conditions, cycling/rate performances are listed in tables. See DOI: 10.1039/c4nr05519e



10 A g⁻¹) as an anode in LIBs, outperforming those of the prepared MoS₂/G, MoS₂/NGurea using urea as a nitrogen source, as well as previously reported MoS₂/C,⁴⁰⁻⁴³ MoS₂/ graphene,³⁰⁻³⁹ MoS₂/N-doped graphene,¹¹ N-doped graphene based metal oxides.^{10,12,13}

The overall synthetic procedure of MoS₂/NG_{g-C,N4} is illustrated in Scheme 1. Polycondensation of urea at 550 °C led to the formation of g-C₃N₄, which was then treated with HCl to produce protonated g-C₃N₄ (g-C₃N₄-H⁺) nanosheets.⁴⁶⁻⁴⁸ GO and g-C₃N₄-H⁺ were flocculated together via sonication (g-C₃N₄-H⁺/GO) (Fig. S1[†]) and fed with Na₂MoO₄ to adsorb MoO₄²⁻. After addition of Na₂S and HCl, the tri-constituent aggregate of MoS₃/g-C₃N₄-H⁺/GO was collected as precipitate and thermally treated at 550 °C in N2 for 3 hours to yield MoS₂/NG_{g-C₂N₄. In controlled experiments, another hybrid of} MoS₂ on N-doped graphene (MoS₂/NGurea) was obtained by directly using urea as a nitrogen source, while a hybrid of MoS₂ on graphene (MoS₂/G) was prepared under the above conditions without involving g-C₃N₄-H⁺ (see ESI[†]). Notably, the synthesis of MoS₂/NG_{g-C₃N₄} can be readily scaled up via our approach (Fig. S1[†]).

As indicated by the X-ray diffraction (XRD) patterns of $MoS_2/NG_{g-C_3N_4}$, MoS_2/G and $MoS_2/NGurea$ (Fig. 1), all of their diffractions are indexed as the hexagonal phase MoS_2 (PDF: 65–1951). Among them, MoS_2/G and $MoS_2/NGurea$ show broad peaks in the 2θ range of 8.8–17.8° with the corresponding *d*-spacings of 0.5–1.0 nm. In contrast, $MoS_2/NG_{g-C_3N_4}$ exhibits a highly crystallized structure with a (002) peak centered at 13.4° and a *d*-spacing of 0.66 nm, which is slightly larger than 0.62 nm for bulk MoS_2 .⁴⁹ Notably, MoS_3/g - C_3N_4 -H⁺/GO as the precursor of $MoS_2/NG_{g-C_3N_4}$ shows two wide peaks at 14.5° and 42° for amorphous MoS_3 ,^{50,52} and a peak at 27.8° for (002) stacking of CN-conjugated layers from g-C_3N_4-H⁺.⁴⁶⁻⁴⁸ However, no characteristic peaks of g-C_3N_4-H⁺ are observed for $MoS_2/NG_{g-C_3N_4}$, implying that g-C_3N_4-H⁺ in MoS_3/g -C_3N_4-H⁺/GO has been decomposed during the thermal treatment.

The morphologies of $g-C_3N_4-H^+/GO$, $MoS_3/g-C_3N_4-H^+/GO$ and $MoS_2/NG_{g-C_3N_4}$ were investigated by scanning electron microscopy equipped with energy dispersive X-ray analysis (SEM/EDX), transmission electron microscopy (TEM) and atomic force microscopy (AFM). As shown in Fig. 2a and S3,†



Fig. 1 XRD patterns of $g-C_3N_4$, $MoS_3/g-C_3N_4-H^+/GO$, $MoS_2/NG_{g-C_3N_4}$, MoS_2/G , MoS_2/NG urea and bare MoS_2 .



Fig. 2 TEM images of (a) $g-C_3N_4-H^+/GO$; (b) $MoS_3/g-C_3N_4-H^+/GO$; (c) SEM image; (d) EDX with elemental mapping; (e) TEM; and (f) HRTEM images of $MoS_2/NG_{g-C_3N_4}$.

g-C₃N₄-H⁺/GO exhibits a 2D sheet-like structure with g-C₃N₄-H⁺ nanosheets attached on the surface of GO. Such assembly behavior should be driven by the electrostatic attraction between the negatively charged GO and the positively charged g-C₃N₄-H⁺ (in aqueous solution, Zeta potential: -33 mV for 0.25 mg L⁻¹ GO; +10 mV for 0.5 mg L⁻¹ g-C₃N₄-H⁺) (Fig. S2†), along with π - π interactions between their analogous aromatic



Fig. 3 HRTEM images of (a) $MoS_2/NG_{g-C_3N_4}$; (b) MoS_2/G ; (c) $MoS_2/NG_{g-C_3N_4}$; (d) nitrogen adsorption–desorption isotherms of $MoS_2/NG_{g-C_3N_4}$, MoS_2/G and MoS_2/NG urea.

frameworks. AFM study further shows thicknesses of 0.96 and 23-34 nm for GO and g-C₃N₄-H⁺/GO, respectively (Fig. S4⁺), verifying that g-C₃N₄-H⁺ nanosheets are successfully decorated on the surface of GO. TEM images manifest that MoS₃ nanoparticles with diameters of around 5 nm are homogeneously decorated on MoS₃/g-C₃N₄-H⁺/GO (Fig. 2b and S5⁺). After pyrolysis, MoS₂/NG_{g-C₂N₄} is featured with a flexible 2D structure inherited from the morphology of MoS₃/g-C₃N₄-H⁺/GO (Fig. 2c, 2e, S6 and S7[†]). EDX and elemental mapping images further disclose that Mo, S, N, C and O elements are homogeneously distributed on MoS₂/NG_{g-C₂N₄} nanosheets (Fig. 2d). High-resolution TEM (HRTEM) images of MoS₂/NG_{g-C₂N₄} reveal that MoS₂ nanoplatelets are vertically aligned on the surface. With lengths less than 10 nm, these nanoplatelets contain few stacked layers (3-10) and a uniform *d*-spacing of 0.66 nm that is consistent with the XRD result (Fig. 2f, 3a, S8[†] and Fig. 1). In contrast, MoS₂/G and MoS₂/NGurea only possess MoS₂ nanosheets with irregular lateral sizes and broad *d*-spacings (Fig. 3b, 3c, S9 and S10[†]) that verify their poor crystallinities along the (002) stacking direction, which might be due to the restrain of the graphene substrate.34,36,39 These results also indicate that g-C₃N₄-H⁺ in the combined MoS₃/g-C₃N₄-H⁺/GO precursor can assist the formation of small and highly crystallized MoS₂ on graphene during the thermal pyrolysis.

Meso-scaled pores are observed among MoS_2 nanoplatelets on $MoS_2/NG_{g-C_3N_4}$ (Fig. 2f, 3a, S8†), thereby the porosity was examined by nitrogen physisorption measurement. The adsorption–desorption isotherm of $MoS_2/NG_{g-C_3N_4}$ exhibits a type IV adsorption branch with a H3 hysteresis loop, which is characteristic of the mesoporous structure (Fig. 3d). Calculated by the DFT method, the pore size distribution of $MoS_2/NG_{g-C_3N_4}$ is in the range of 4–30 nm (Fig. S12†). The corresponding Brunauer–Emmett–Teller (BET) surface area and the total pore volume are calculated to be 109 m² g⁻¹ and 0.883 cm³ g⁻¹, respectively, which are much higher than those of MoS₂/G (39 m² g⁻¹ and 0.1267 cm³ g⁻¹), MoS₂/NGurea (100 m² g⁻¹ and 0.1267 cm³ g⁻¹) and other reported MoS₂ based materials (30–90 m² g⁻¹ and 0.1–0.44 m³ g⁻¹).^{32,37,40,41}

Thermogravimetric analysis (TGA) under a N2 atmosphere was conducted to understand the formation of MoS₂/NG_{g-C-N}. As shown in Fig. S13,[†] pure MoS₃ exhibits ca. 18 wt% loss between 380 and 430 °C, corresponding to the conversion of $MoS_3(v_1) \rightarrow MoS_2(v)+S.^{50,52}$ Without the presence of MoS_3 , the decomposition of g-C₃N₄-H⁺ in g-C₃N₄-H⁺/GO occurs at 600-750 °C, which is in accordance with reported results for g-C₃N₄.^{27,51} Strikingly, the tri-constituent composite of $MoS_3/$ g-C₃N₄-H⁺/GO undergoes substantial weight losses at low temperatures of 350-400 °C and 500-580 °C, assigned to the MoS₃ pyrolysis and g-C₃N₄-H⁺ decomposition, respectively. This result suggests that there are synergistic interactions between molybdenum sulfides (MoS_3/MoS_2) and g-C₃N₄-H⁺ during the thermal treatment that promotes the decompositions of both MoS₃ and g-C₃N₄-H⁺.^{52,53} Upon treatment of MoS₃/g-C₃N₄-H⁺/ GO at 400 °C in N₂ for 3 h, the coexistence of MoS₂ and g-C₃N₄ can be observed in the resulting material (Fig. S14†), while, the absence of g-C₃N₄-H⁺ features in XRD and Fourier Transform Infrared (FTIR) spectra of MoS₂/NG_{g-C₂N₄} (Fig. 1 and S15[†]) demonstrates the complete decomposition of g-C₃N₄-H⁺ in $MoS_3/g-C_3N_4-H^+/GO$ after treated at 550 °C in N₂ for 3 h. During the g-C₃N₄-H⁺ decomposition, massive gas containing cyano fragments (e.g. $C_2N_2^+$, $C_3N_2^+$, and $C_3N_3^+$)⁵⁴ might be generated from the surface of graphene, which can not only control the growth of MoS₂ from MoS₃ pyrolysis into small size nanocrystals, but also serve as the nitrogen-rich source to dope graphene with N at a mild temperature of 550 °C. During the formation of MoS₂, the N-enriched graphene substrate can disturb the growth of layered MoS₂ crystals, especially in the (002) plane.^{11,34} As a result, the nanocrystals of MoS_2 are vertically grown on the surface of graphene. The weight percentage of MoS_2 in the resulting $MoS_2/NG_{g-C_2N_4}$ is *ca.* 70 wt%, based on the TGA under air (Fig. S16†).

X-ray photoelectron spectroscopy (XPS) was applied to analyze the chemical states of the elements in $MoS_2/NG_{g-C_3N_4}$, MoS₂/G, and MoS₂/NGurea, respectively. For MoS₂/NG_{g-C-N}, the N content in graphene is about 13 at%, which ranks at the top of the reported N-doped graphenes (0.2-10 at%) (Fig. S18, Table S1[†]).⁷⁻²⁸ High-resolution N 1s spectra further disclose that three N configurations with 30% graphitic N (401.6 eV), 55% pyridinic N (398.4 eV) and 15% pyrrolic N (400 eV) are presented in the N-enriched graphene (Fig. 4a). In contrast, with a very high feed ratio of urea (see ESI[†]), MoS₂/NGurea obtained at 550 °C possesses 12 at% N, while there are only 5% graphitic N along with 76% pyridinic N and 19% pyrrolic N (Fig. 4c, S19[†]). In general, the formation of graphitic N inside the graphene framework is much more difficult than introducing pyridinic and pyrrolic N atoms on the edges/ defects. High temperature treatment (700-1100 °C) is usually required to improve the amount of graphitic N,7,9,22,25,26,28 which nevertheless will lead to massive loss of the total nitrogen content (Table S1[†]). In our work, the substantial for-



Fig. 4 Core-level XPS spectra of (a) N 1s and Mo 2p; (b) Mo 3d and S 2s of $MoS_2/NG_{g-C_3N_4}$; (c) graphitic, pyrrolic and pyridinic N fractions of $MoS_2/NG_{g-C_3N_4}$ and $MoS_2/NGurea$. (d) Raman spectra of MoS_2/G , $MoS_2/NGurea$ and $MoS_2/NG_{q-C_4N_4}$.

mation of graphitic N in $MOS_2/NG_{g-C_3N_4}$ at 550 °C can be stemmed from the complete decomposition of $g-C_3N_4-H^+$ attached on GO promoted by molybdenum sulfide. Graphitic N has proven to favor the electron transfer from N to the adjacent C atoms and reduce the adsorption energy of lithium, which are desired for LIBs applications.^{8,9} In addition, Mo $3d_{5/2}$ and $3d_{3/2}$ peaks appearing at 229.58 and 232.68 eV for $MOS_2/NG_{g-C_3N_4}$ are lower than 229.64 and 232.83 eV for MOS_2/G (Fig. 4b, S20†), indicating that there is an electron delocalization from the N-enriched graphene to the coupled MOS_2 .

Raman characterizations further studied the coupling effect between MoS₂ and graphene in MoS₂/G, MoS₂/NGurea and MoS₂/NG_{g-C₃N₄. As shown in Fig. 4d, two peaks at 378 and 402 cm⁻¹ for MoS₂/G are assigned to the in-plane E_{2g}^1 and outof-plane A_{1g} modes of hexagonal MoS₂. However, MoS₂/ NGurea and MoS₂/NG_{g-C₃N₄} only possess strong signals for E_{2g}^1 mode. The peak of A_{1g} mode is weakened for MoS₂/NGurea and even disappeared for MoS₂/NG_{g-C₃N₄. It has been evidenced that the signal of the A_{1g} mode for MoS₂ can be significantly softened and broadened by external factors such as substrates or electron doping.^{55,56} The Raman results demonstrate the enormously enhanced coupling between MoS₂ and the N-enriched graphene in MoS₂/NG_{g-C₃N₄.}}}

The electrochemical performances of $MoS_2/NG_{g-G_3N_4}$, $MoS_2/NGurea$ and MoS_2/G as anodes in LIBs were first investigated by cyclic voltammogram (CV). As shown in Fig. 5a, in the first cathodic scan, the 1.01 V peak is assigned to the Li⁺ intercalation into MoS_2 layers for forming Li_xMOS_2 , 34,39 0.36 V peak is attributed to the reduction of Li_xMOS_2 to Mo and Li_2S . 34,37,39 In the anodic scans, the peaks around 1.70 and 2.28 V can be associated with the conversions of Mo to MoS_2 along with Li_2S to polysulfide, respectively. 34,38,39 In the subsequent cathodic scans, three reductive peaks appearing at 1.95, 1.25 and 0.40 V are attributed to $2Li^+ + S + 2e^- \rightarrow Li_2S$, $MoS_2 + xLi^+ + xe^- \rightarrow$



Fig. 5 CV curves at a scanning rate of 0.1 mV s⁻¹ of the first 5 cycles for (a) $MOS_2/NG_{g-C_3N_{4'}}$ (b) MOS_2/NG urea and (c) MOS_2/G ; charging–discharging curves at 0.1 A g⁻¹ of the first 10 cycles for (d) $MOS_2/NG_{g-C_3N_{4'}}$ (e) MOS_2/NG urea and (f) MOS_2/G .

Li_xMoS₂, and Li_xMoS₂ + $(4 - x)Li^+ + (4 - x)e^- \rightarrow 2Li_2S + Mo$, respectively.^{34,37} It is notable that the peak at 1.25 V of MoS₂/ NG_{g-G₃N₄} for MoS₂ + $xLi^+ + xe^- \rightarrow Li_xMoS_2$ is much sharper than those of MoS₂/G (0.98 V) and MoS₂/NGurea (1.08 V). Besides, the potential differences between the pairs of oxidative/reductive peaks measured with 0.45 V (Δ 1) and 0.33 V (Δ 2) for MoS₂/NG_{g-G₃N₄} are much smaller than those for MoS₂/ G (0.72, 0.49 V), MoS₂/NGurea (0.62, 0.48 V) (Fig. 5a–c) or the reported MoS₂/N-graphene using ammonia as the nitrogen source,¹¹ demonstrating that MoS₂/NG_{g-C₃N₄} possesses the best reversibility of the lithiation/delithiation conversions and the lowest internal diffusion resistance.⁵⁷

 $MoS_2/NG_{g-G_3N_4}$, MoS_2/G and MoS_2/NG urea were further evaluated by galvanostatic charge–discharge cycling at 0.1 A g⁻¹. As shown in Fig. 5d, the plateaus on the charge/discharge curves of $MoS_2/NG_{g-G_3N_4}$ are in good agreement with the conversion peaks on its CV (Fig. 5a). Different from MoS_2/G and MoS_2/NG urea, $MoS_2/NG_{g-G_3N_4}$ shows right shifted charge/discharge curves with increasing capacities along the 2–10 cycles in the whole voltage range of 0.01–3 V (Fig. 5d–f), presenting its increasing reversibility of the lithiation/delithiation during the initial cycles. This result might be associated with the mesoporous surface of $MoS_2/NG_{g-G_3N_4}$ that allows an efficient electrode–electrolyte contact and an effective activation of the N defects for Li storage.^{11,12} As shown in Fig. 6a, $MoS_2/NG_{g-G_3N_4}$ exhibits first and second discharge capacities of 1728 and 1200 mA h g⁻¹, which increases to 1450 mA h g⁻¹ with as



Fig. 6 (a) Variation of charge/discharge specific capacities *versus* cycle number for $MoS_2/NG_{g-C_sN_{a'}} MoS_2/NGurea$, MoS_2/G at 0.1 A g⁻¹ for 200 cycles; (b) specific capacities *versus* cycle number for $MoS_2/NG_{g-C_sN_{a'}} MoS_2/NGurea$, MoS_2/G at 0.1, 0.2, 0.5, 1, 2, 5, 10 A g⁻¹.

high as 84% retention of the first discharge capacity and then retains for 200 cycles. In contrast, MOS_2/G delivers first and second discharge capacities of 1043 and 826 mA h g⁻¹, which decreases to 405 mA h g⁻¹ after 200 cycles with only 39% of the first discharge capacity. Although the prepared MOS_2/NG urea also shows good stability, the delivered capacities (800 mA h g⁻¹) with 67% of the first discharge capacity (1200 mA h g⁻¹) are much lower than those of $MOS_2/NG_{g-C_3N_4}$. It is notable that the high surface area of $MOS_2/NG_{g-C_3N_4}$ has not increased its side reaction with an electrolyte as other reported materials with a large capacity loss,⁵⁸ which should be due to the least irreversible Li⁺ consumption by stable SEI formation on the surface of the strong coupled nanosheet.

Rate performances of $MoS_2/NG_{g-C_3N_4}$, MoS_2/G and MoS_2/NG NGurea were examined at various current densities in the range of 0.1–10 A g⁻¹ (Fig. 6b). Reversible capacities of around 1220–1310, 1300, 1230, 1200, 1100, 960 mA h g⁻¹ are achieved for $MoS_2/NG_{g-C_3N_4}$ at 0.1, 0.2, 0.5, 1, 2 and 5 A g⁻¹, respectively. Remarkably, as high as 92% of the 1310 mA h g⁻¹ at 0.1 A g⁻¹ is retained at 1 A g⁻¹ with 1200 mA h g⁻¹. The charge/discharge process can be even completed within 4 min at an ultrahigh current density of 10 A g⁻¹ with a remarkable capacity of 830 mA h g⁻¹, which is more than twice the theoretical

capacity of graphite. Upon resetting the current density to 0.1 A g⁻¹, a reversible capacity of around 1460 mA h g⁻¹ is restored that even surpasses the capacities during the initial 10 cycles, which should take into account the activation process. In contrast, both MoS₂/G and MoS₂/NGurea deliver inferior capacities of 840, 620, 330 mA h g⁻¹ and 820, 500, 160 mA h g⁻¹ at 0.1, 1, 10 A g⁻¹, respectively. As summarized in Table S2,† the exceptional capacity and rate capability of MoS₂/NG_{g-C₃N₄ also outstrip those of the previously reported MoS₂/C (369–986 mA h g⁻¹ at 1 A g⁻¹),^{40–43} MoS₂/graphene (500–1040 mA h g⁻¹ at 1 A g⁻¹),¹⁰ other N-graphene based composites with SnO₂, Fe₃O₄ (683–994 mA h g⁻¹ at 1 A g⁻¹),^{10,12,13} and tubular TiO₂ (114, 164 mA h g⁻¹ at 5 A g⁻¹).}

Kinetic differences of MoS₂/NGg-C3N4, MoS₂/G and MoS₂/ NGurea electrodes were investigated by electrochemical impedance spectroscopy (EIS) after 30 cycles. As shown in Fig. 7a, the high-frequency semicircle corresponds to the solid SEI film resistance (R_f) and the constant phase element (CPE1), the semicircle in the medium-frequency region is assigned to the charge-transfer impedance (R_{ct}) and the constant phase element of the electrode-electrolyte interface (CPE2), and Z_{W} is associated with the Warburg impedance. Obviously, MoS₂/ NGg-C2N4 possesses more depressed semicircles at high frequencies. The SEI film resistance (R_f) and charge-transfer resistance (R_{ct}) for MoS₂/NG_{g-C₃N₄} based on the modified equivalent circuit (Inset of Fig. 7a) are fitted to be 12.3 and 9.2 Ω , which are significantly lower than those of MoS₂/G (204.8 and 14.33 Ω) and MoS₂/NGurea (70.9 and 27.7 Ω). These results confirm that the N-enriched graphene substrate in $MoS_2/NG_{g-C_3N_4}$ has distinctively boosted the electronic conductivity of the hybrid. Besides, the strong coupled com-



Fig. 7 (a) Nyquist plots of $MOS_2/NG_{g-C_3N_4'}$, MOS_2/G and MOS_2/NG urea electrodes, the inset is the equivalent circuit model of the studied system; SEM image of the electrodes after 200 cycles for (b) $MOS_2/NG_{g-C_3N_4}$; (c) MOS_2/G , the insets are the corresponding EDX spectra, F and P elements are from the composition of the SEI layer.

ponents in $MOS_2/NG_{g-C_3N_4}$ nanosheets should be responsible for stable Li⁺ conductive SEI layer formation (Fig. 7b) with reduced contact resistance, allowing rapid electron transport for high electrochemical performance.⁵⁸

From above, the super lithium storage performance of MoS₂/NG_{2-C₂N₂} can be attributed to the synergistic effects from MoS₂ and N-enriched graphene: first, highly crystallized layered MoS₂ nanoplatelets vertically exposed on the nanosheets and rich content of N dopants in the underlying graphene can provide abundant accessible active sites for lithium intercalation and chemical adsorption,^{9-13,29} resulting in the excellent capacities. Second, the high content of N dopants distributed on defects/edges and inside of graphene obtained from pyrolysis of the assembled precursor (MoS₃/ g-C₃N₄-H⁺/GO) has significantly enhanced its coupling with MoS₂ dispersed on the surface, which renders the ultra-long cycle life by efficiently prohibiting the aggregation or detachment of the active MoS₂ on graphene during cycling. As shown in Fig. S21,† Mo species are well dispersed on the nanosheets after 200 charge/discharge cycles of MoS₂/NG_{g-C₂N₄}³⁰ whereas, MoS₂/G suffers from severe aggregations (Fig. 7b and S22[†]). Another merit of the strong coupled architecture is the effectively reduced interfacial resistance within the hybrid, along with the N enriched graphene as the electrical highway, the intrinsic electronic conductivity of the whole hybrid is largely boosted that is beneficial for ultrafast charging/discharging. Additionally, the architecture of mesoporous nanosheets with a high surface area is beneficial for the electrode-electrolyte contact and facilitates ion diffusions.

Conclusions

In summary, we have developed a facile and efficient strategy to construct a novel 2D hybrid of MoS₂/NG_{g-C,N4} by the mild temperature (550 °C) pyrolysis of assembled MoS₃/g-C₃N₄-H⁺/ GO. Benefiting from the architecture of mesoporous nanosheets with highly crystallized MoS2 nanoplatelets strongly coupled on N-enriched graphene, boosted electron/ ion transportation and rich lithium storage sites are achieved. As a result, the $MoS_2/NG_{g-C_3N_4}$ based LIB anode manifests small side reaction with an electrolyte, excellent capacities with long term stability (1450 mA h g^{-1} at 0.1 A g^{-1} for 200 cycles) and extraordinary rate capabilities (1200 mA h g^{-1} at 1A g^{-1} , 830 mA h g^{-1} at 10 A g^{-1}). More importantly, the presented strategy provides a new avenue towards the large-scale production of strongly coupled N-enriched graphene based hybrids for various energy applications including Na/Mg batteries, fuel cells, supercapacitors, etc.

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